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Matsumoto et al.

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(54) **POWER SEMICONDUCTOR DEVICE**

(71) Applicant: **MITSUBISHI ELECTRIC CORPORATION**, Tokyo (JP)

(72) Inventors: **Manabu Matsumoto**, Tokyo (JP); **Yoshitaka Otsubo**, Tokyo (JP); **Hiroyuki Masumoto**, Tokyo (JP)

(73) Assignee: **Mitsubishi Electric Corporation**, Tokyo (JP)

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(30) **Foreign Application Priority Data**

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(51) **LOC (11) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/182, 103, 110, 118, 123, 124, 133, D13/145–147, 149, 152, 154, 173, 175, D13/184, 199
CPC H01L 23/04; H01L 23/055; H01L 23/48; H01L 23/552; H01L 25/18; H01L 25/50; H01L 23/24; H01R 12/585; H05K 5/02; H05K 7/00; H05K 7/14; H05K 7/1427; H05K 7/1435; H05K 5/00
See application file for complete search history.

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Primary Examiner — Thomas Johannes
Assistant Examiner — Shawn T Gingrich
(74) *Attorney, Agent, or Firm* — Studebaker & Brackett PC

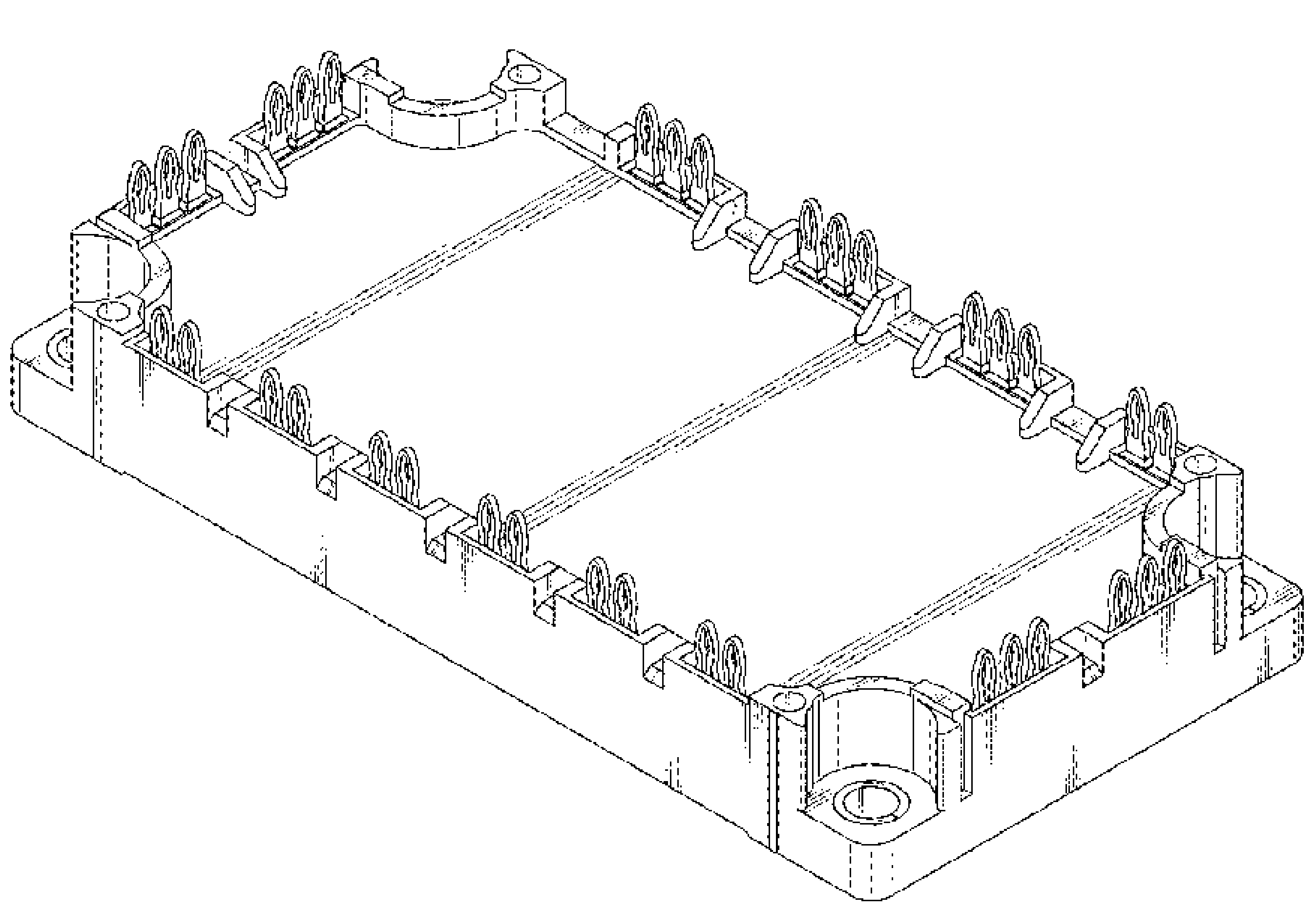
(57) **CLAIM**

The ornamental design for a power semiconductor device, as shown and described.

DESCRIPTION

FIG. **1** is a front, top and right side perspective view of a power semiconductor device, showing our new design;
FIG. **2** is a rear, bottom and left side perspective view thereof;
FIG. **3** is a front view thereof;
FIG. **4** is a rear view thereof;
FIG. **5** is a top view thereof;
FIG. **6** is a bottom view thereof;
FIG. **7** is a left side view thereof; and,
FIG. **8** is right side view thereof.
The broken line portion of the figure drawings is included to show portions of the article that form no part of the claimed design.

1 Claim, 5 Drawing Sheets



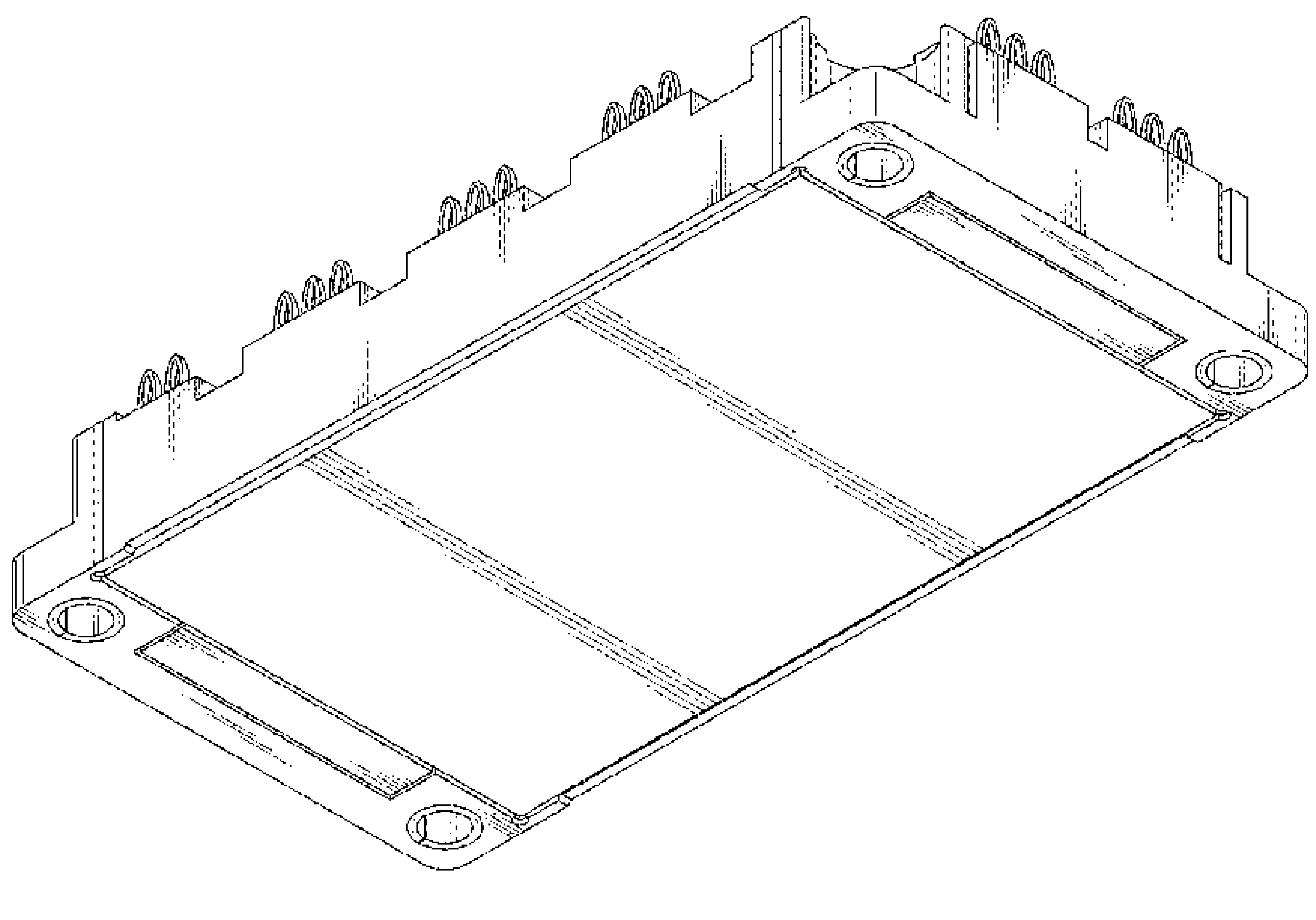


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Fig. 1

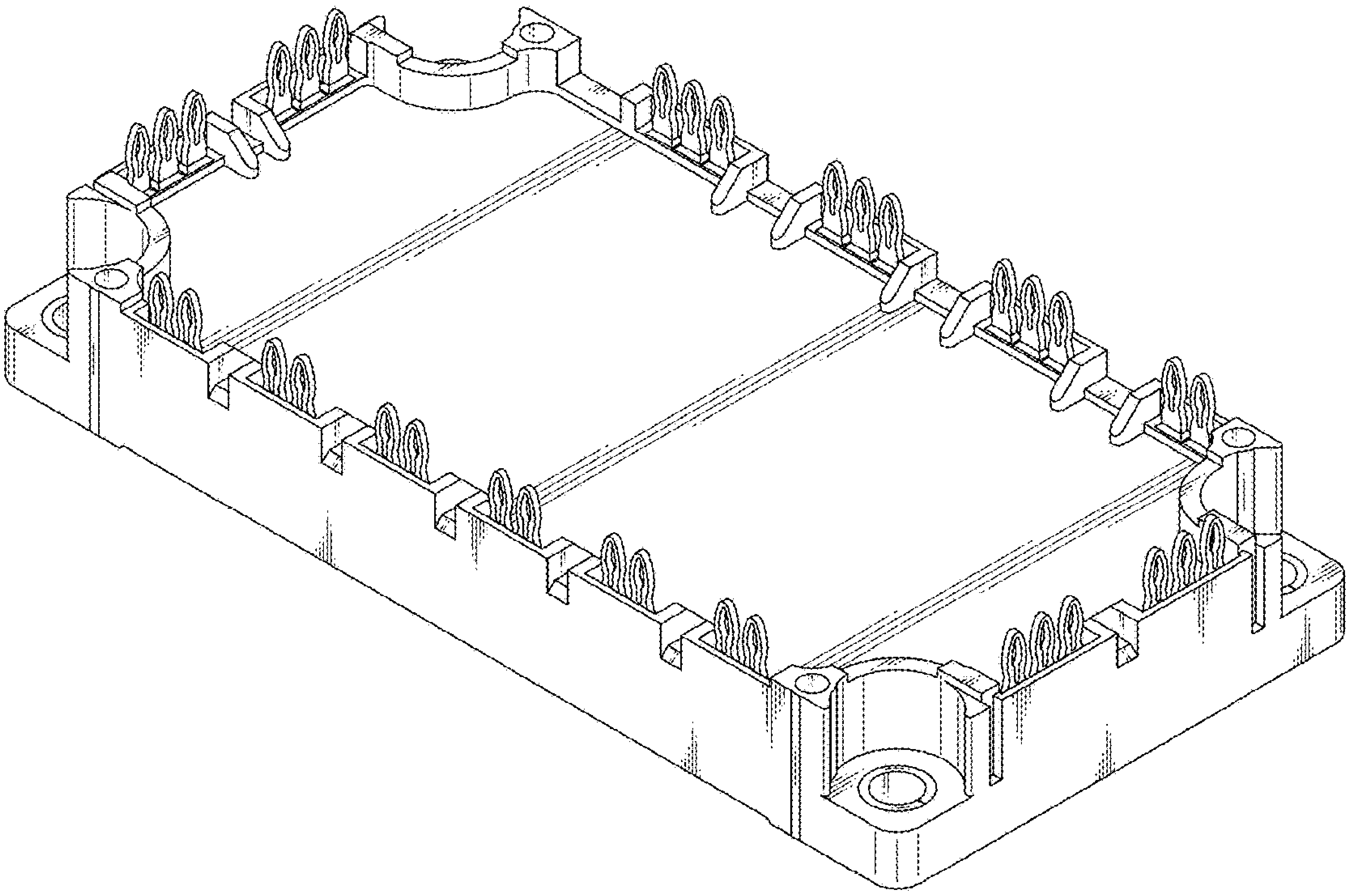


Fig. 2

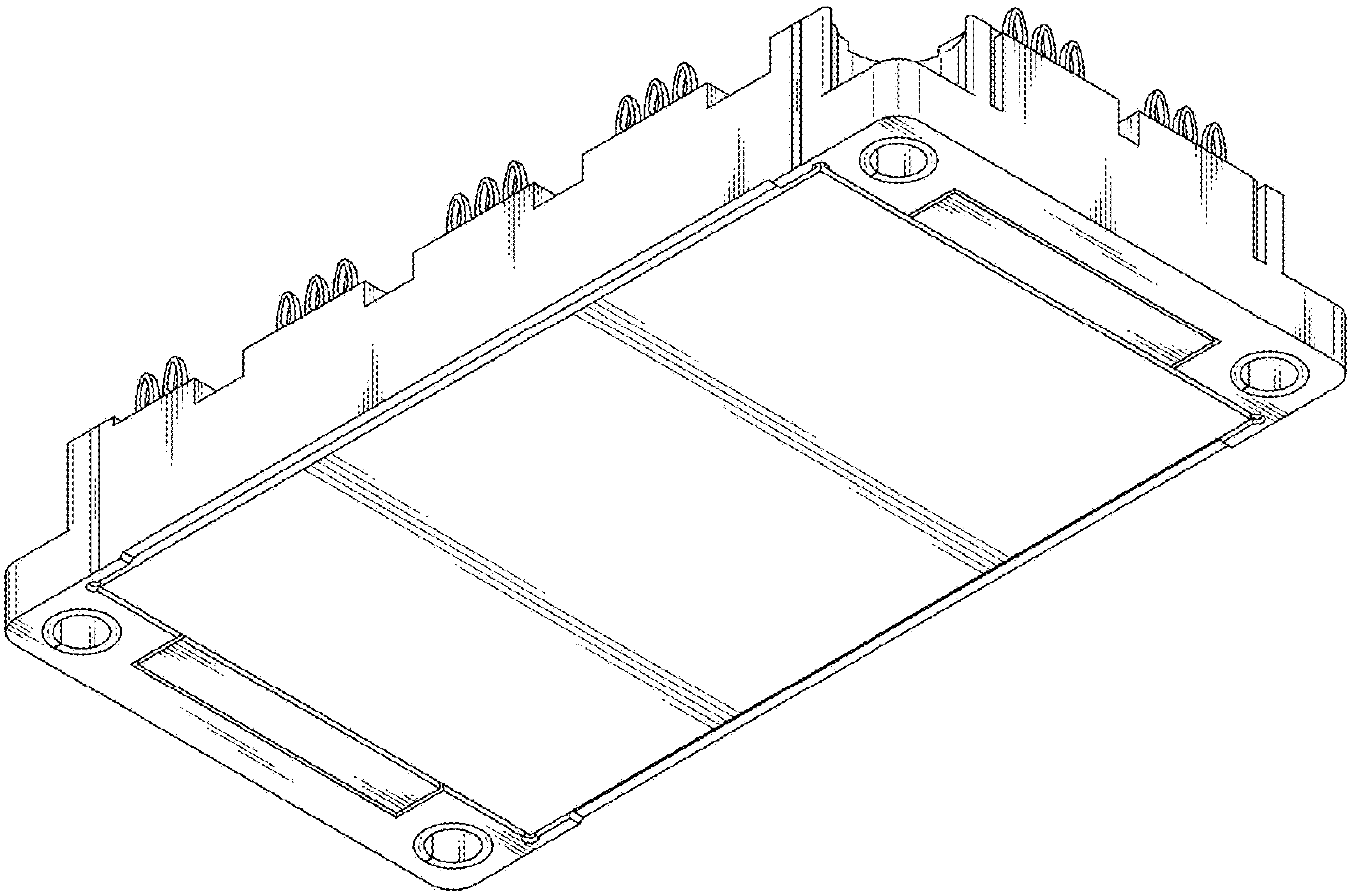


Fig. 3

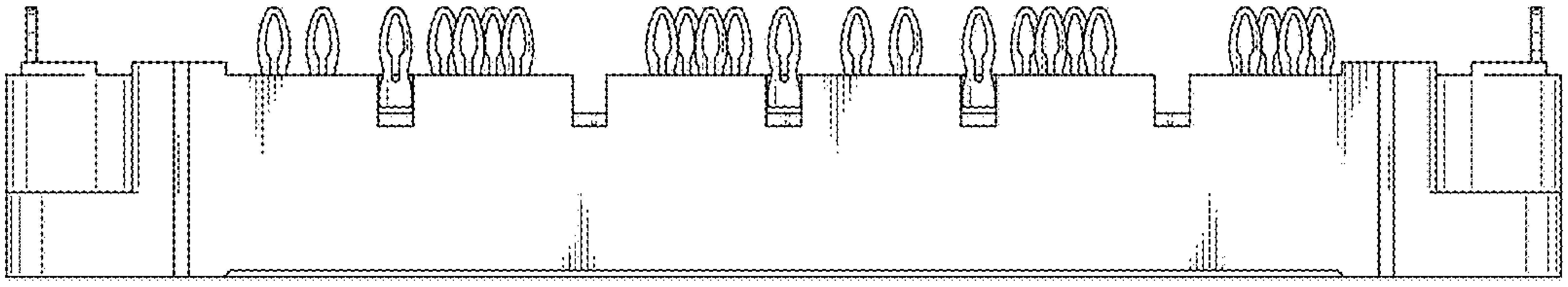
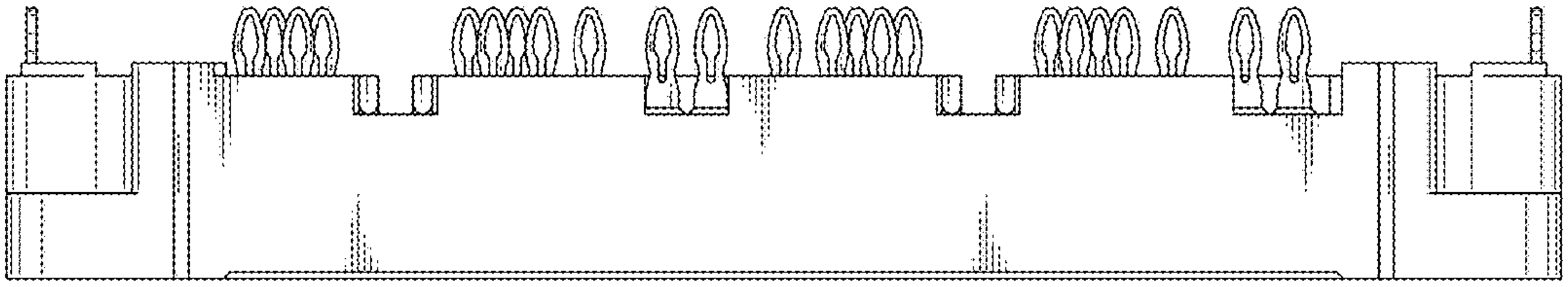


Fig. 4



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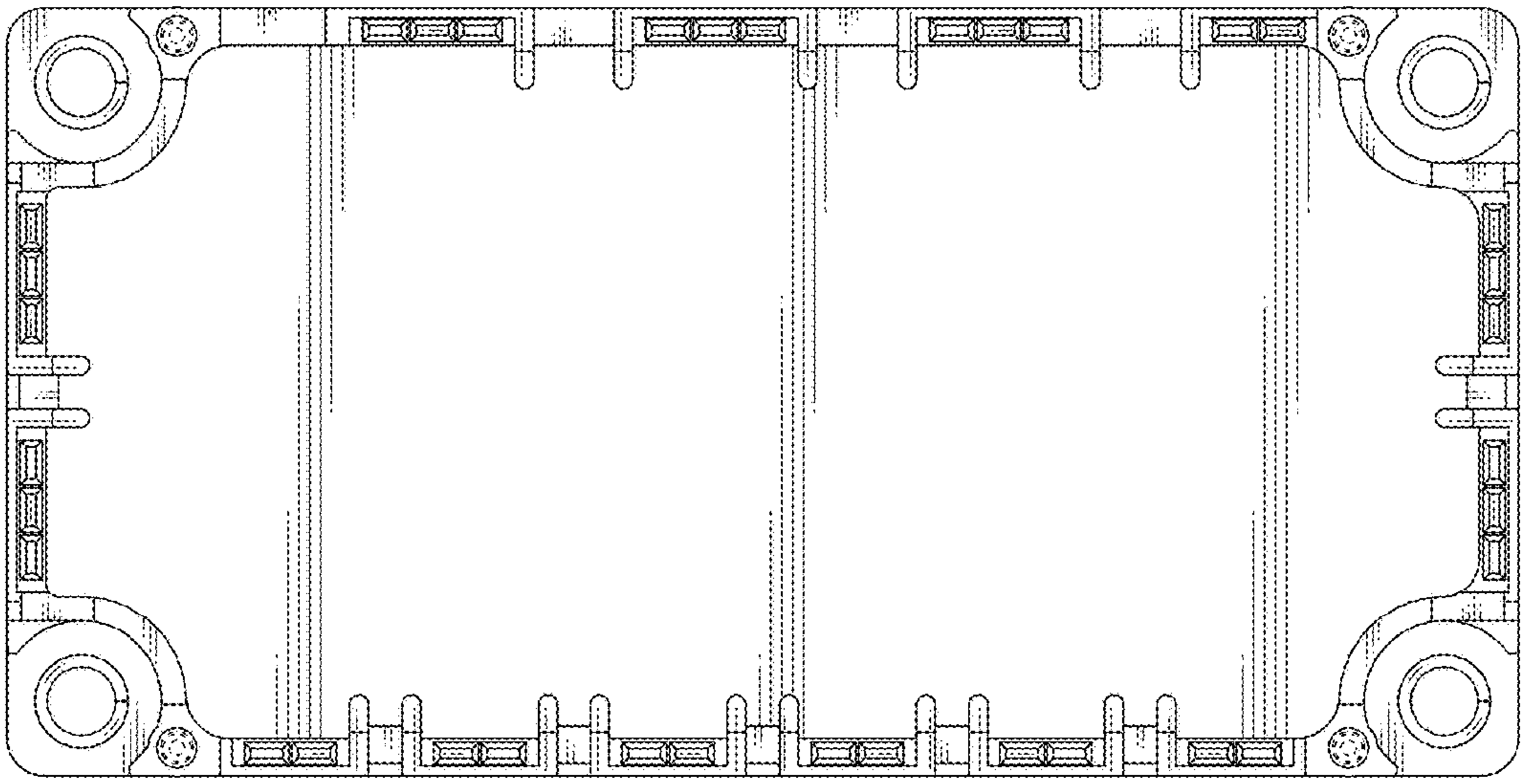

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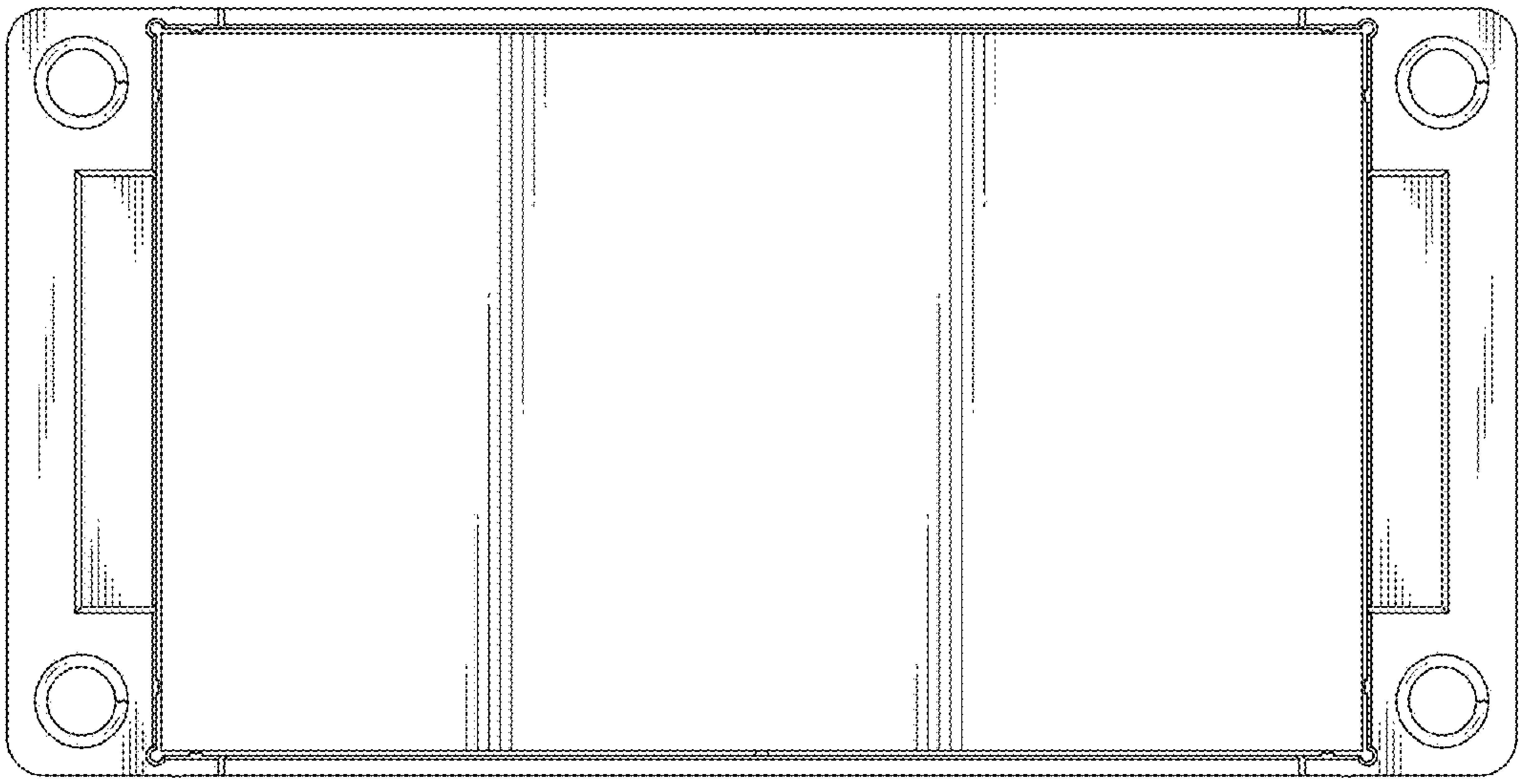

Fig. 7

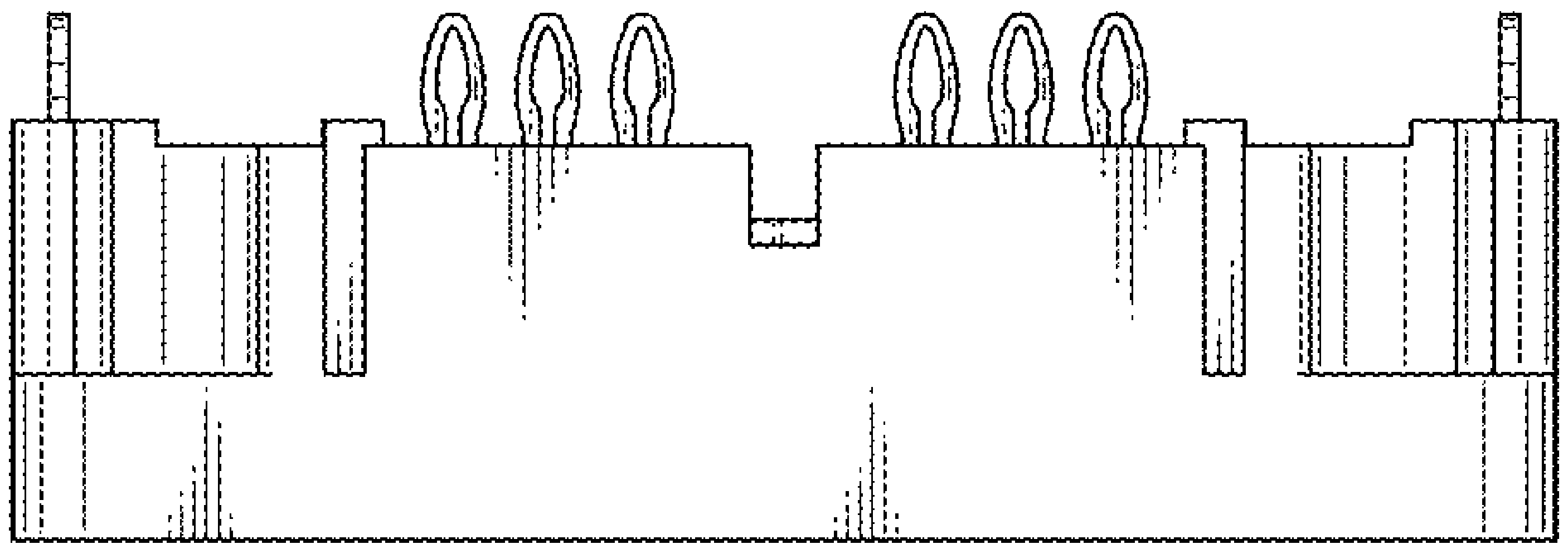

Fig. 8